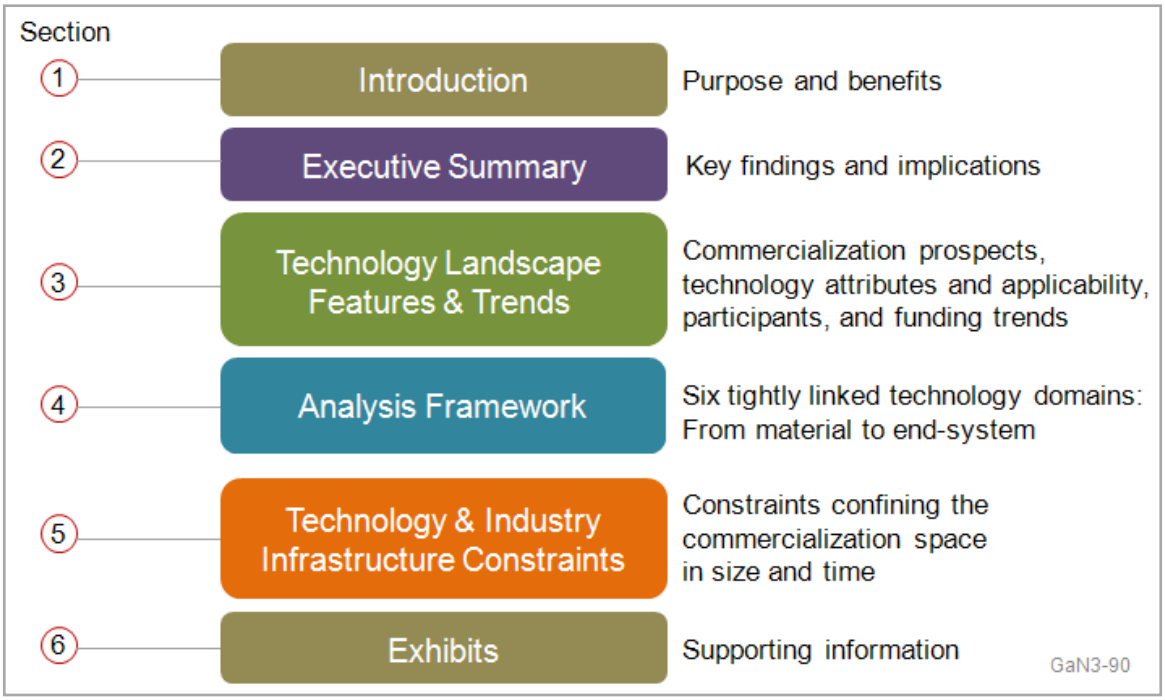
SAN JOSE, CA – April 22, 2013 – Venture-Q announces its new Technology Status & Issues report, the third of a six-report set dedicated to the commercialization of GaN-on-Si technology for power conversion applications.

This report delivers comprehensive and up-to-date (as of March 2013) insights not only into the present status of GaN-on-Si technology, but also relevant issues and their impact on the commercialization timeline. The scope of this report serves as the basis for assessing market penetration rate, size, and timing. In the case of a radically new technology such as GaN-on-Si for power conversion applications, understanding of technology and industry infrastructure constraints is a prerequisite for a meaningful and more realistic estimation of addressable market size and timing.

The report's five major sections highlight a number of key topics that factor into the status of GaN-on-Si technology. Provided information is up-to-date as of March 2013.

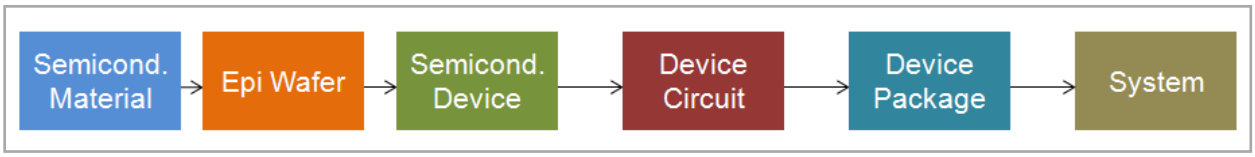


SECTION 3 scopes features and trends of the power technology landscape from a range of technology commercialization aspects, including:

- Present technology status and attributes, which include power technologies and products, participating semiconductor vendors and R&D/academic institutions, market penetration and segmentation aspects, as well as funding sources and trends
- End-equipment applications aspects, which include technology value proposition and VQ model used to identify high potential market opportunities
- Commercialization timing aspects, which include exploration, demonstration, and production phases of the 2005 to 2025 period

SECTION 4 introduces VQ analysis framework, which facilitates assessments of the GaN-on-Si technology status and issues as well as the technology commercialization prospects.

The framework features six tightly linked technology domains, including (1) semiconductor material, (2) epi wafer, (3) semiconductor device (discrete and IC), (4) device circuit, (5) packaging (single/multichip and module), and (6) end-equipment system. In-depth analyses of each domain reveal the GaN-on-Si value proposition, competing technologies and products, as well as constrains limiting a large scale market penetration.

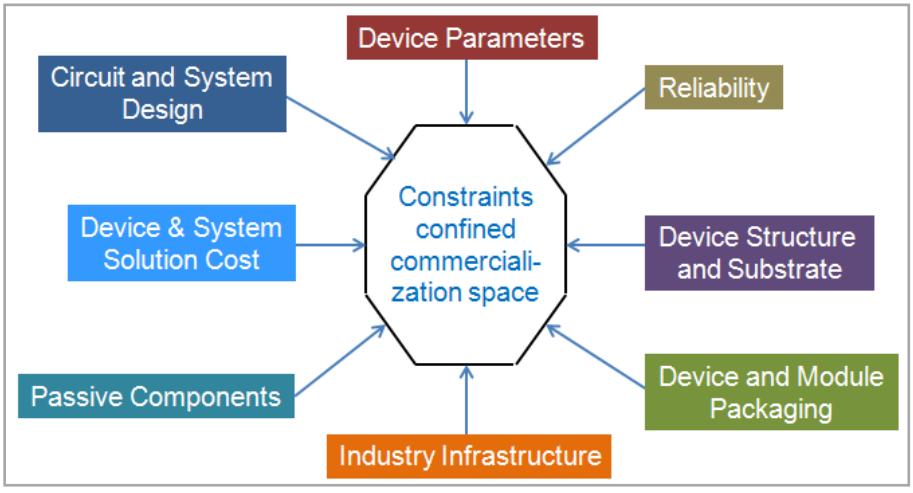


In addition, this section introduces and quantifies ten key device and manufacturing differentiators of high voltage GaN-on-Si HEMT technology. These include device performance attributes and reliability, and device and manufacturing cost.

This section also covers the monolithic integration (IC) of GaN and Si devices, which represents a distinct competitive advantage over the present high voltage and power silicon technologies.

SECTION 5 addresses eight areas of technology and industry infrastructure constraints, which confine the commercialization space in both size and time. Industry's ability to reduce or remove these constraints strongly influences both the size and timing of the addressable market, in addition to competitive aspects of silicon technologies.

The areas of constraints include GaN-on-Si power devices, passives, packaging, circuit and system design, reliability, cost, and industry infrastructure.



About Technology Status & Issues report

Publication date: April 2013. The report price is $5,950.00. For multiple report discounts, please contact VQ@venture-Q.com or +1 408 300 1494 (Tel) or +1 408 440 1716 (Fax). Reports are delivered via e-mail as PDF files.